TOSHIBA

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT Process)

# 2SC2236

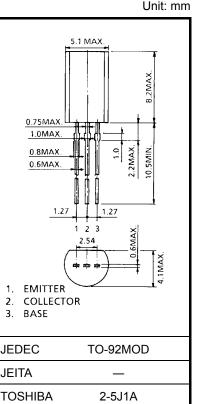
### Audio Power Amplifier Applications

Complementary to 2SA966 and 3-watt output applications. •

## Absolute Maximum Ratings (Ta = 25°C)

| Characteristics             | Symbol           | Rating     | Unit |
|-----------------------------|------------------|------------|------|
| Collector-base voltage      | V <sub>CBO</sub> | 30         | V    |
| Collector-emitter voltage   | V <sub>CEO</sub> | 30         | V    |
| Emitter-base voltage        | V <sub>EBO</sub> | 5          | V    |
| Collector current           | Ι <sub>C</sub>   | 1.5        | А    |
| Base current                | Ι <sub>Β</sub>   | 0.15       | А    |
| Collector power dissipation | P <sub>C</sub>   | 900        | mW   |
| Junction temperature        | Tj               | 150        | °C   |
| Storage temperature range   | T <sub>stg</sub> | −55 to 150 | °C   |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.



Weight: 0.36 g (typ.)

Please design the appropriate reliability upon reviewing the

Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

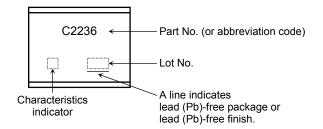
#### Unit: mm

Electrical Characteristics (Ta = 25°C)

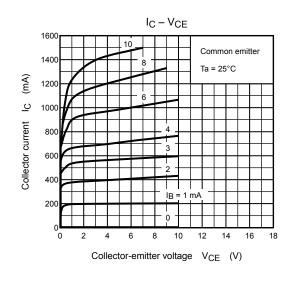
| Characteristics                      | Symbol                    | Test Condition  | Min | Тур. | Max | Unit |
|--------------------------------------|---------------------------|---|-----|------|-----|------|
| Collector cut-off current            | I <sub>CBO</sub>          | V <sub>CB</sub> = 30 V, I <sub>E</sub> = 0            | —   | _    | 100 | nA   |
| Emitter cut-off current              | I <sub>EBO</sub>          | V <sub>EB</sub> = 5 V, I <sub>C</sub> = 0             | -   | _    | 100 | nA   |
| Collector-emitter breakdown voltage  | V (BR) CEO                | I <sub>C</sub> = 10 mA, I <sub>B</sub> = 0            | 30  | _    | _   | V    |
| Emitter-base breakdown voltage       | V (BR) EBO                | I <sub>E</sub> = 1 mA, I <sub>C</sub> = 0             | 5   | _    | _   | V    |
| DC current gain                      | h <sub>FE</sub><br>(Note) | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 500 mA        | 100 | _    | 320 |      |
| Collector-emitter saturation voltage | V <sub>CE (sat)</sub>     | I <sub>C</sub> = 1.5 A, I <sub>B</sub> = 0.03 A       | _   |      | 2.0 | V    |
| Base-emitter voltage                 | V <sub>BE</sub>           | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 500 mA        | -   | _    | 1.0 | V    |
| Transition frequency                 | fT                        | V <sub>CE</sub> = 2 V, I <sub>C</sub> = 500 mA        | _   | 120  | -   | MHz  |
| Collector output capacitance         | C <sub>ob</sub>           | V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz |     | _    | 30  | pF   |

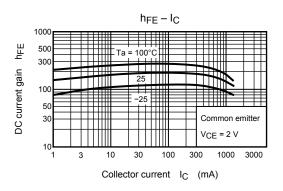
Note: h<sub>FE</sub> classification O: 100 to 200, Y: 160 to 320

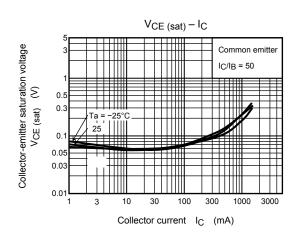
# Marking

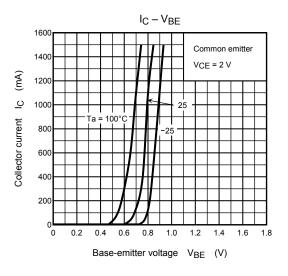


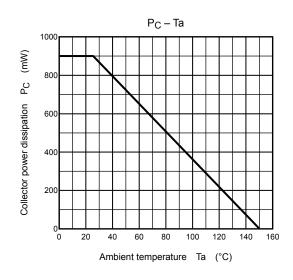
# **TOSHIBA**

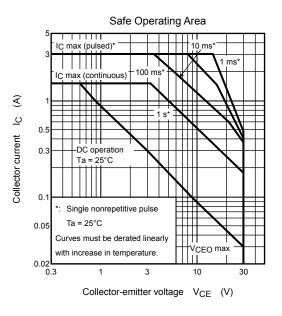












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